

HA5023/883

Dual 125MHz Video Current Feedback Amplifier

January 1995

Features

• This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.

Wide Unity Gain Bandwidth	125MHz
• Slew Rate	475V/μs
Differential Gain	0.03%
Differential Phase	0.03 Deg.
• Supply Current (per Amplifier)	7.5mA
Crosstalk Rejection at 10MHz	60dB
• ESD Protection	20001

• Guaranteed Specifications at ± 5 V Supplies

Applications

- Video Gain Block
- Video Distribution Amplifier/RGB Amplifier
- · Flash A/D Driver
- **Current to Voltage Converter**
- · Radar and Imaging Systems
- · Medical Imaging

Description

The HA5023/883 is a dual version of the popular Intersil HA-5020/883 except that it does not have an enable function. It features wide bandwidth and high slew rate, and is optimized for video applications and gains between 1 and 10. It is a current feedback amplifier and thus yields less bandwidth degradation at high closed loop gains than voltage feedback amplifiers.

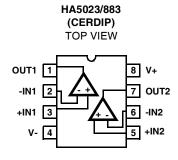
The low differential gain and phase, 0.1dB gain flatness, and ability to drive two back terminated 75Ω cables, make this amplifier ideal for demanding video applications.

The current feedback design allows the user to take advantage of the amplifier's bandwidth dependency on the feedback resistor. By reducing R_{F} , the bandwidth can be increased to compensate for decreases at higher closed loop gains or heavy output loads.

Ordering Information

PART NUMBER	TEMPERATURE RANGE	PACKAGE
HA5023MJ/883	-55°C to +125°C	8 Lead CerDIP

Pinout



Specifications HA5023/883

Absolute Maximum Ratings Thermal Information

Voltage Between V+ and V
Differential Input Voltage 10V
Voltage at Either Input TerminalV+ to V-
Output Current Fully Short Circuit Protected
Junction Temperature
ESD Rating< 2000V
Storage Temperature Range -65° C $\leq T_{A} \leq +150^{\circ}$ C

Lead Temperature (Soldering 10s). +300°C

Thermal Resistance	$\theta_{\sf JA}$	θ _{JC} 28°C/W
CerDIP Package	115°C/W	28°C/W
Maximum Package Power Dissipation at		
CerDIP Package		0.87W
Package Power Dissipation Derating Fac	tor above +7	5°C
CerDIP Package		8.7mW/°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Operating Conditions

Operating Supply Voltage ($\pm V_S$) $\pm 5V$ to $\pm 15V$ V_{INCM} $\leq 1/2(V+-V-)$ Operating Temperature Range. $55^{\circ}C \leq T_A \leq +125^{\circ}C$ R_L $\check{S} \geq 50\Omega$ R_F = $1k\Omega$

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_{SOURCE} = 0\Omega$, $R_L = 400\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

			GROUP A		LIMITS			
PARAMETERS	SYMBOL	CONDITIONS	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS	
Input Offset Voltage	V_{IO}	V _{CM} = 0V	1	+25°C	-3	3	mV	
			2, 3	+125°C, -55°C	-5	5	mV	
Common Mode	CMRR	$\Delta V_{CM} = \pm 2.5 V$	1	+25°C	53	-	dB	
Rejection Ratio		V+ = 2.5V, V- = -7.5V V+ = 7.5V, V- = -2.5V	2	+125°C	38	-	dB	
		$\Delta V_{CM} = \pm 2.25V$ V+ = 2.75V, V- = -7.25V V+ = 7.25V, V- = -2.75V	3	-55°C	38	-	dB	
Power Supply	PSRR	$\Delta V_{SUP} = \pm 1.5V$	1	+25°C	60	-	dB	
Rejection Ratio		V+ = 6.5V, V- = -5V V+ = 3.5V, V- = -5V	2, 3	+125°C, -55°C	55	-	dB	
Delta Input Offset	ΔV_{IO}	V _{CM} = 0	1	+25°C	-	3.5	mV	
Voltage Between Channels			2,3	+125°C, -55°C	-	3.5	mV	
Non-Inverting Input	I _{BSP}	V _{CM} = 0V	1	+25°C	-8	8	μΑ	
(+IN) Current			2, 3	+125°C, -55°C	-20	20	μΑ	
+IN Current Common	CMS _{IBP}	$\Delta V_{CM} = \pm 2.5 V$	1	+25°C	-	0.15	μ A /V	
Mode Sensitivity		V+ = 2.5V, V- = -7.5V V+ = 7.5V, V- = -2.5V	2	+125°C	-	2.0	μ A /V	
		$\Delta V_{CM} = \pm 2.25V$ V+ = 2.75V, V- = -7.25V V+ = 7.25V, V- = -2.75V	3	-55°C	-	2.0	μ A /V	
ΔInverting Input (-IN)	ΔI_{BSN}	V _{CM} = 0	1	+25°C	-15	15	μΑ	
Current Between Channels			2, 3	+125°C, -55°C	-30	30	μΑ	
Inverting Input (-IN)	I _{BSN}	V _{CM} = 0V	1	+25°C	-12	12	μΑ	
Current			2, 3	+125°C, -55°C	-30	30	μΑ	
-IN Current Common	CMS _{IBN}	$\Delta V_{CM} = \pm 2.5 V$	1	+25°C	-	0.4	μ A /V	
Mode Sensitivity		V+ = 2.5V, V- = -7.5V V+ = 7.5V, V- = -2.5V	2	+125°C	-	5	μ A /V	
		ΔV _{CM} = ±2.25V V+ = 2.75V, V- = -7.25V V+ = 7.25V, V- = -2.75V	3	-55°C	-	5	μ A /V	

Specifications HA5023/883

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_{SOURCE} = 0\Omega$, $R_L = 400\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

			GROUP A		LIMITS			
PARAMETERS	SYMBOL	CONDITIONS	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS	
-IN Current Power	PSS _{IBN}	$\Delta V_{SUP} = \pm 1.5V$	1	+25°C	-	0.2	μ A /V	
Supply Sensitivity		V+ = 6.5V, V- = -5V V+ = 3.5V, V- = -5V	2, 3	+125°C, -55°C	-	0.5	μ A /V	
+IN Current Power	PSS _{IBP}	$\Delta V_{SUP} = \pm 1.5V$	1	+25°C	-	0.1	μ A /V	
Supply Sensitivity		V+ = 6.5V, V- = -5V V+ = 3.5V, V- = -5V	2, 3	+125°C, -55°C	-	0.3	μ A /V	
Output Voltage	V _{OP}	$A_V = +1$ $V_{IN} = -3V$	1	+25°C	2.5	-	V	
Swing		$R_{L} = 150\Omega \frac{V_{IN} = -3V}{V_{IN} = -3V}$	2, 3	+125°C, -55°C	2.5	-	V	
	V _{ON}	A .4 \/ .0\/	1	+25°C	-	-2.5	V	
		$R_{L} = 150\Omega \frac{V_{IN} = +3V}{V_{IN} = +3V}$	2, 3	+125°C, -55°C	-	-2.5	V	
Short Circuit Output	+I _{SC}	$V_{IN} = \pm 2.5V$	1	+25°C	50	-	mA	
Current		V _{OUT} = 0V	2, 3	+125°C, -55°C	50	-	mA	
	$V_{IN} = \pm 2.5V$ $V_{OUT} = 0V$		1	+25°C	-	-40	mA	
		V _{OUT} = 0V	2, 3	+125°C, -55°C	-	-40	mA	
Output Current +I _{OU1}	+l _{OUT}	Note 1	1	+25°C	20	-	mA	
			2, 3	+125°C, -55°C	16.6	-	mA	
	-l _{out}	Note 1	1	+25°C	-	-20	mA	
			2, 3	+125°C, -55°C	-	-16.6	mA	
Quiescent Power	I _{cc}	$R_L = 400\Omega$	1	+25°C	-	10	mA/Op Amp	
Supply Current			2, 3	+125°C, -55°C	-	10	mA/Op Amp	
	I _{EE}	$R_L = 400\Omega$	1	+25°C	-10	-	mA/Op Amp	
			2, 3	+125°C, -55°C	-10	-	mA/Op Amp	
Transimpedance	+A _{ZOL1}	$R_L = 400\Omega$	1	+25°C	1	-	MΩ	
		$V_{OUT} = \pm 2.5V$	2, 3	+125°C	0.5	-	MΩ	
		V _{OUT} = ±2.25V	3	-55°C	0.5	-	MΩ	
	-A _{ZOL1}	$R_L = 400\Omega$	1	+25°C	1	-	МΩ	
		$V_{OUT} = \pm 2.5V$	2, 3	+125°C	0.5	-	MΩ	
		V _{OUT} = ±2.25V	3	-55°C	0.5	-	MΩ	

NOTF:

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

Table 2 Intentionally Left Blank.

^{1.} Guaranteed from $\rm V_{OUT}$ Test with $\rm R_L$ = 150 $\!\Omega,$ by: $\rm I_{OUT}$ = $\rm V_{OUT}/150 \,\Omega.$

Specifications HA5023/883

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: $V_{SUPPLY} = \pm 5V$, $A_V = +2$, $R_F = 681\Omega$, $R_L = 400\Omega$, Unless Otherwise Specified.

					LIMITS		
PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
-3dB Bandwidth	BW(+1)	$A_V = +1$, $R_F = 1K$ $V_{OUT} = 100 \text{mV}_{RMS}$	1	+125°C, -55°C	62	-	MHz
	BW(+2)	$A_V = +2,$ $V_{OUT} = 100 \text{mV}_{RMS}$	1	+125°C, -55°C	62	-	MHz
Gain Flatness	GF5	$A_V = +2$, f \leq 5MHz $V_{OUT} = 100mV_{RMS}$	1	+125°C, -55°C	-	±0.045	dB
	GF10	$A_V = +2, f \le 10MHz$ $V_{OUT} = 100mV_{RMS}$	1	+125°C, -55°C	-	±0.085	dB
	GF20	$A_V = +2$, f \leq 20MHz $V_{OUT} = 100mV_{RMS}$	1	+125°C, -55°C	-	±0.65	dB
Slew Rate	+SR(+1)	A _V = +1, R _F = 1K V _{OUT} = -2V to +2V	1, 4	+125°C, -55°C	250	-	V/μs
	-SR(+1)	A _V = +1, R _F = 1K V _{OUT} = +2V to -2V	1, 4	+125°C, -55°C	240	-	V/μs
	+SR(+2)	$A_V = +2$, $V_{OUT} = -2V$ to $+2V$	1, 4	+125°C, -55°C	400	-	V/µs
	-SR(+2)	$A_V = +2$, $V_{OUT} = +2V$ to $-2V$	1, 4	+125°C, -55°C	360	-	V/μs
Rise and Fall Time	T _R	$A_V = +2$, $V_{OUT} = -0.5V$ to $+0.5V$	1, 2	+125°C, -55°C	-	6.5	ns
	T _F	$A_V = +2$, $V_{OUT} = +0.5V$ to $-0.5V$	1, 2	+125°C, -55°C	-	6.5	ns
Overshoot	+OS	$A_V = +2$, $V_{OUT} = -0.5V$ to $+0.5V$	1, 3	+125°C, -55°C	-	35	%
	-OS	$A_V = +2$, $V_{OUT} = +0.5V$ to $-0.5V$	1, 3	+125°C, -55°C	-	27	%
Propagation Delay	+T _P	A_V = +2, R_F = 681 Ω V_{OUT} = 0V to 1V	1, 2	+125°C, -55°C	-	9.5	ns
	-T _P	$A_V = +2$, $R_F = 681\Omega$ $V_{OUT} = 1V$ to $0V$	1, 2	+125°C, -55°C	-	9.0	ns

NOTES:

- 1. Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot-to-lot and within lot variation.
- 2. Measured between 10% and 90% points.
- 3. For 200ps input transition times. Overshoot decreases as input transition times increase, especially for A_V = +1. Please refer to Performance Curves.
- 4. Measured between 25% and 75% points.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLE 1)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1 (Note 1), 2, 3, 4
Group A Test Requirements	1, 2, 3, 4
Groups C and D Endpoints	1

NOTE:

1. PDA applies to Subgroup 1 only.

Test Circuits and Waveforms

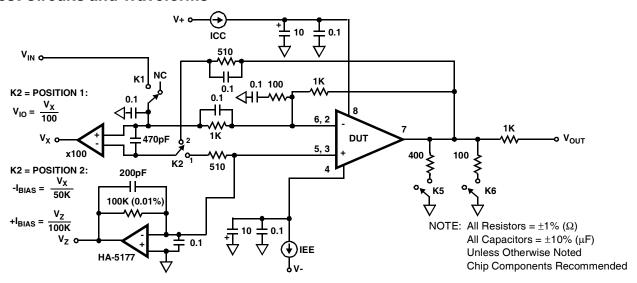


FIGURE 1. TEST CIRCUIT (Applies to Table 1)

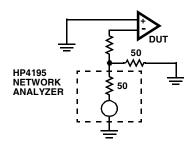


FIGURE 2. TEST CIRCUIT FOR TRANSIMPEDANCE MEASUREMENTS

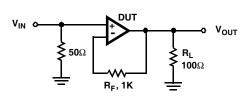


FIGURE 3. SMALL SIGNAL PULSE RESPONSE CIRCUIT

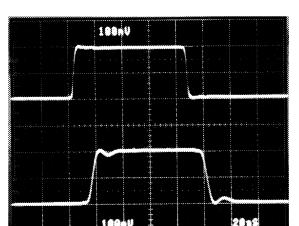


FIGURE 5. SMALL SIGNAL RESPONSE
Vertical Scale: V_{IN} = 100mV/Div., V_{OUT} = 100mV/Div.
Horizontal Scale: 20ns/Div.

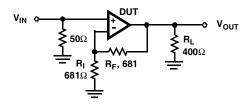
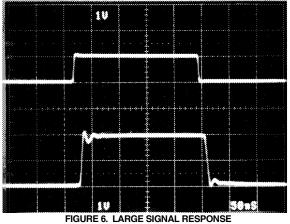


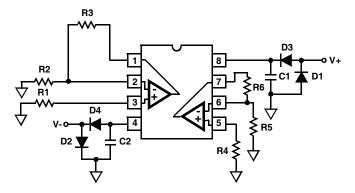
FIGURE 4. LARGE SIGNAL PULSE RESPONSE CIRCUIT



Vertical Scale: V_{IN} = 1V/Div., V_{OUT} = 1V/Div. Horizontal Scale: 50ns/Div.

Burn-In Circuit

HA5023MJ/883 CERAMIC DIP



NOTES:

 $R1 = R2 = R4 = R5 = 1k\Omega$, $\pm 5\%$ (Per Socket)

 $R3 = R6 = 10k\Omega$, $\pm 5\%$ (Per Socket)

 $C1 = C2 = 0.01 \mu F$ (Per Socket) or $0.1 \mu F$ (Per Row) Minimum

D1 = D2 = 1N4002 or Equivalent (Per Board)

D3 = D4 = 1N4002 or Equivalent (Per Socket)

 $V+=+5.5V\pm0.5V$

 $V\text{-}=\text{-}5.5V\pm0.5V$

Die Characteristics

DIE DIMENSIONS:

65 x 100 x 19 mils \pm 1 mils $1650 \ x \ 2540 \ x \ 483 \mu m \pm 25.4 \mu m$

METALLIZATION:

Type: Metal 1: AlCu (1%), Metal 2: AlCu (1%) Thickness: Metal 1: 8kÅ \pm 0.4kÅ, Metal 2: 16kÅ \pm 0.8kÅ

WORST CASE CURRENT DENSITY:

1.9 x 10⁵ A/cm² at 15mA

SUBSTRATE POTENTIAL (Powered Up): V-

GLASSIVATION:

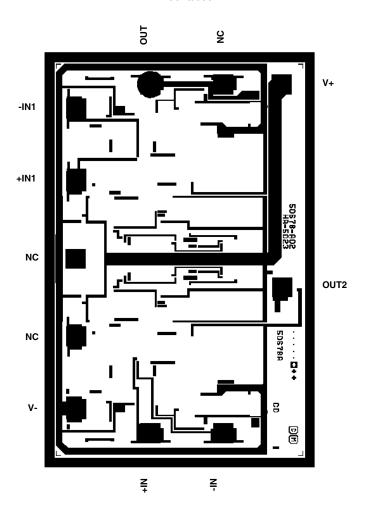
Type: Nitride

Thickness: $4k\mathring{A} \pm 0.4k\mathring{A}$ **TRANSISTOR COUNT: 124**

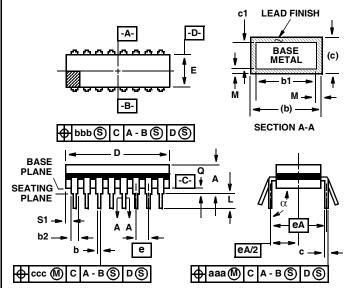
PROCESS: Bipolar Dielectric Isolation

Metallization Mask Layout

HA5023/883



Ceramic Dual-In-Line Frit Seal Packages (CerDIP)



NOTES:

- Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
- The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
- 3. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness.
- Corner leads (1, N, N/2, and N/2+1) may be configured with a partial lead paddle. For this configuration dimension b3 replaces dimension b2.
- 5. This dimension allows for off-center lid, meniscus, and glass overrun.
- 6. Dimension Q shall be measured from the seating plane to the base plane.
- 7. Measure dimension S1 at all four corners.
- 8. N is the maximum number of terminal positions.
- 9. Dimensioning and tolerancing per ANSI Y14.5M 1982.
- 10. Controlling dimension: INCH.

F8.3A MIL-STD-1835 GDIP1-T8 (D-4, CONFIGURATION A) 8 LEAD CERAMIC DUAL-IN-LINE FRIT SEAL PACKAGE

	INC	HES	MILLIM			
SYMBOL	MIN	MAX	MIN	MAX	NOTES	
Α	-	0.200	-	5.08	-	
b	0.014	0.026	0.36	0.66	2	
b1	0.014	0.023	0.36	0.58	3	
b2	0.045	0.065	1.14	1.65	-	
b3	0.023	0.045	0.58	1.14	4	
С	0.008	0.018	0.20	0.46	2	
c1	0.008	0.015	0.20	0.38	3	
D	-	0.405	- 10.29		5	
Е	0.220	0.310	5.59 7.87		5	
е	0.100	0.100 BSC		2.54 BSC		
eA	0.300	BSC	7.62 BSC		-	
eA/2	0.150	BSC	3.81 BSC		-	
L	0.125	0.200	3.18	5.08	-	
Q	0.015	0.060	0.38	1.52	6	
S1	0.005	-	0.13	-	7	
α	90°	105°	90°	105°	-	
aaa	-	0.015	-	0.38	-	
bbb	-	0.030	-	0.76	-	
ccc	-	0.010	-	0.25	-	
М	-	0.0015	-	0.038	2, 3	
N	8	3	8	3	8	

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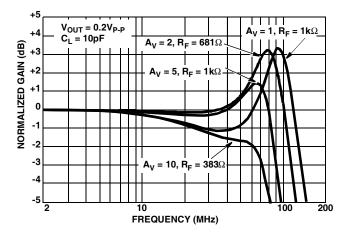
DESIGN INFORMATION

Dual 125MHz Video Current Feedback Amplifier

January 1995

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Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$, Unless Otherwise Specified.



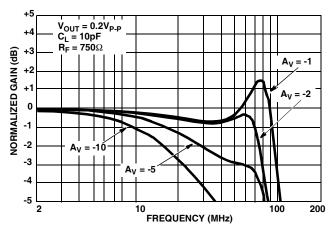


FIGURE 1. NON-INVERTING FREQENCY RESPONSE

180 (DEGREES) $A_V = +1$, $R_F = 1k\Omega$ **NVERTING PHASE (DEGREES)** -45 -90 PHASE (+45 -135 = +10, R_F = 383 $\overline{\Omega}$ -100 NONINVERTING -225 45 -270 90 $A_V = -10, R_F = 750\Omega$ 135 -315 $V_{OUT} = 0.2V_{P-P}$ -360 180 C_L = 10pF FREQUENCY (MHz)

FIGURE 2. INVERTING FREQUENCY RESPONSE

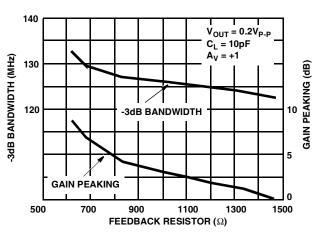
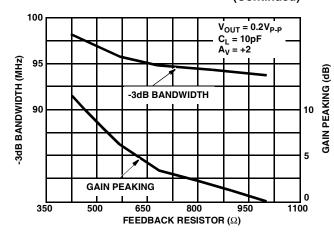


FIGURE 3. PHASE RESPONSE AS A FUNCTION OF FREQUENCY

FIGURE 4. BANDWIDTH AND GAIN PEAKING vs FEEDBACK RESISTANCE

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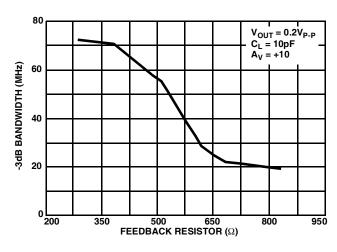
Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$, Unless Otherwise Specified. (Continued)



130 120 3dB BANDWIDTH (MHz) -3dB BANDWIDTH GAIN PEAKING (dB) 110 100 $V_{OUT} = 0.2V_{P-P}$ 90 **GAIN PEAKING** $C_L = 10pF$ A_V = +1 80 ___0 1000 200 400 600 800 LOAD RESISTOR (Ω)

FIGURE 5. BANDWIDTH AND GAIN PEAKING VS FEEDBACK RESISTANCE

FIGURE 6. BANDWIDTH AND GAIN PEAKING vs LOAD RESISTANCE



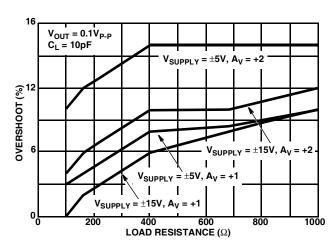
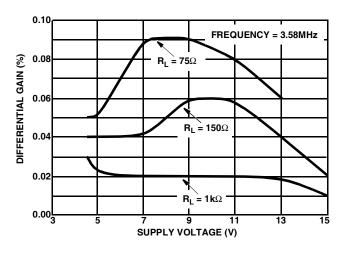


FIGURE 7. BANDWIDTH vs FEEDBACK RESISTANCE

FIGURE 8. SMALL SIGNAL OVERSHOOT VS LOAD RESISTANCE

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Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$, Unless Otherwise Specified. (Continued)



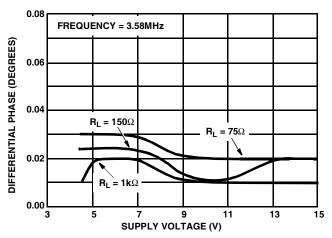
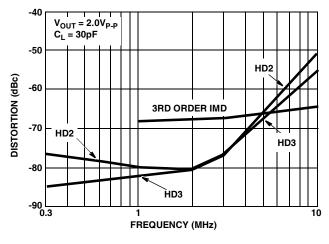


FIGURE 9. DIFFERENTIAL GAIN vs SUPPLY VOLTAGE

FIGURE 10. DIFFERENTIAL PHASE vs SUPPLY VOLTAGE



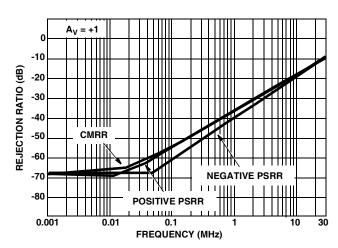
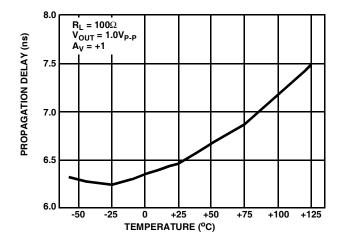


FIGURE 11. DISTORTION vs FREQUENCY

FIGURE 12. REJECTION RATIOS vs FREQUENCY



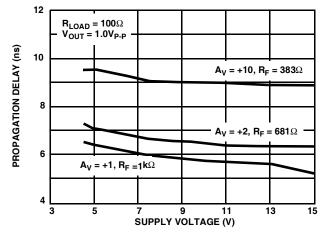
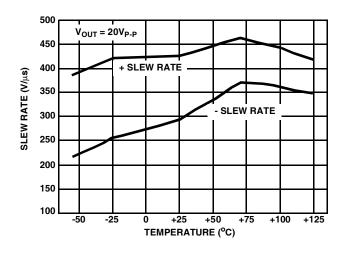


FIGURE 13. PROPAGATION DELAY vs TEMPERATURE

FIGURE 14. PROPAGATION DELAY vs SUPPLY VOLTAGE

The information contained in this section has been developed through characterization by Intersil Corporation and is for use as application and design information only. No guarantee is implied.

Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$, Unless Otherwise Specified. (Continued)



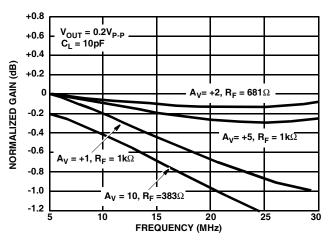
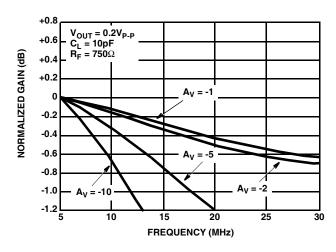


FIGURE 15. SLEW RATE vs TEMPERATURE





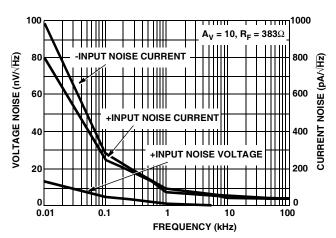
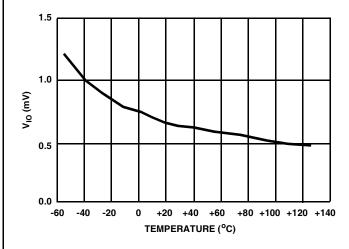


FIGURE 17. INVERTING GAIN FLATNESS vs FREQUENCY

FIGURE 18. INPUT NOISE CHARACTERISTICS



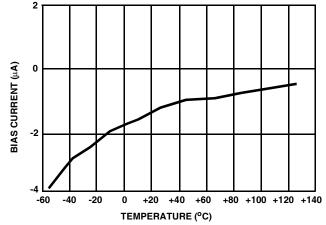
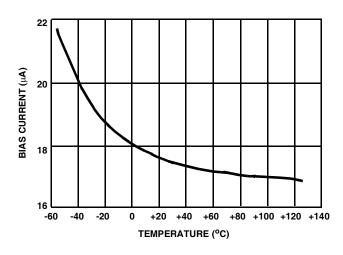


FIGURE 19. INPUT OFFSET VOLTAGE vs TEMPERATURE

FIGURE 20. +INPUT BIAS CURRENT vs TEMPERATURE

The information contained in this section has been developed through characterization by Intersil Corporation and is for use as application and design information only. No guarantee is implied.

Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$, Unless Otherwise Specified. (Continued)



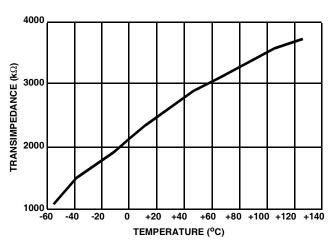


FIGURE 21. -INPUT BIAS CURRENT vs TEMPERATURE

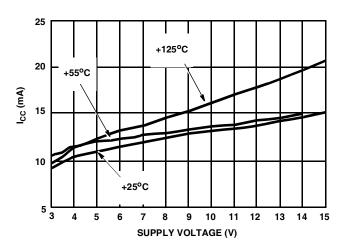


FIGURE 22. TRANSIMPEDANCE vs TEMPERATURE

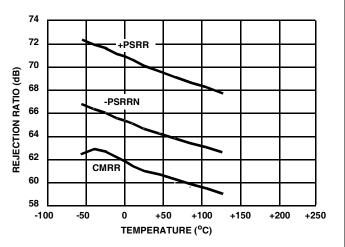


FIGURE 23. SUPPLY CURRENT vs SUPPLY VOLTAGE

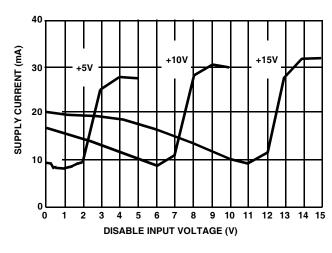


FIGURE 24. REJECTION RATIO vs TEMPERATURE

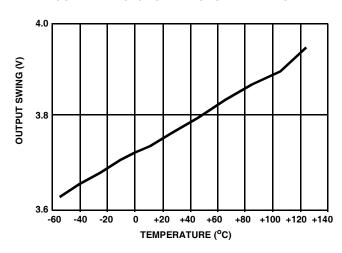
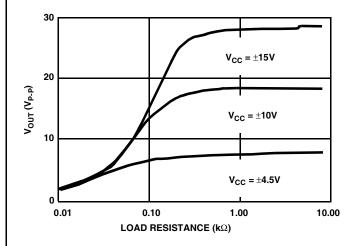


FIGURE 25. SUPPLY CURRENT vs DISABLE INPUT VOLTAGE

FIGURE 26. OUTPUT SWING vs TEMPERATURE

Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$, Unless Otherwise Specified. (Continued)



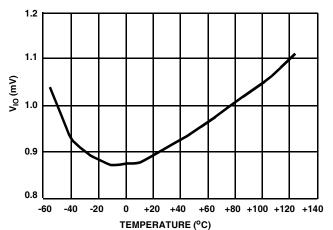
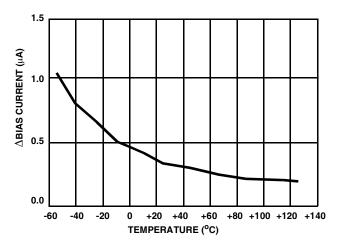


FIGURE 27. OUTPUT SWING vs LOAD RESISTANCE

FIGURE 28. INPUT OFFSET VOLTAGE CHANGE BETWEEN CHANNELS vs TEMPERATURE



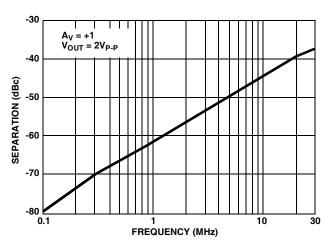
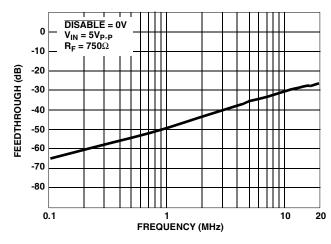


FIGURE 29. INPUT BIAS CURRENT CHANGE BETWEEN CHANNELS vs TEMPERATURE

FIGURE 30. CHANNEL SEPARATION vs FREQUENCY



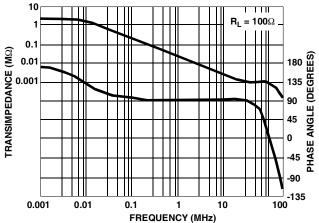


FIGURE 31. DISABLE FEEDTHROUGH vs FREQUENCY

FIGURE 32. TRANSIMPEDANCE vs FREQUENCY

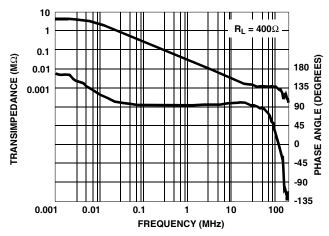


FIGURE 33. TRANSIMPEDENCE vs FREQUENCY

The information contained in this section has been developed through characterization by Intersil Corporation and is for use as application and design information only. No guarantee is implied.

Application Information

Optimum Feedback Resistor

The plots of inverting and non-inverting frequency response, see Figure 1 and Figure 2 in the typical performance section, illustrate the performance of the HA5023 in various closed loop gain configurations. Although the bandwidth dependency on closed loop gain isn't as severe as that of a voltage feedback amplifier, there can be an appreciable decrease in bandwidth at higher gains. This decrease may be minimized by taking advantage of the current feedback amplifier's unique relationship between bandwidth and R_F. All current feedback amplifiers require a feedback resistor, even for unity gain applications, and R_F, in conjunction with the internal compensation capacitor, sets the dominant pole of the frequency response. Thus, the amplifier's bandwidth is inversely proportional to R_F. The HA5023 design is optimized for a 1000Ω R_F at a gain of +1. Decreasing R_F in a unity gain application decreases stability, resulting in excessive peaking and overshoot. At higher gains the amplifier is more stable, so R_F can be decreased in a trade-off of stability for bandwidth.

The table below lists recommended R_F values for various gains, and the expected bandwidth.

GAIN (A _{CL})	R _F (Ω)	BANDWIDTH (MHz)
-1	750	100
+1	1000	125
+2	681	95
+5	1000	52
+10	383	65
-10	750	22

PC Board Layout

The frequency response of this amplifier depends greatly on the amount of care taken in designing the PC board. The use of low inductance components such as chip resistors and chip capacitors is strongly recommended. If leaded components are used the leads must be kept short especially for the power supply decoupling components and those components connected to the inverting input.

Attention must be given to decoupling the power supplies. A large value (10 μ F) tantalum or electrolytic capacitor in parallel with a small value (0.1 μ F) chip capacitor works well in most cases.

A ground plane is strongly recommended to control noise. Care must also be taken to minimize the capacitance to ground seen by the amplifier's inverting input (-IN). The larger this capacitance, the worse the gain peaking, resulting in pulse overshoot and possible instability. It is recom-

mended that the ground plane be removed under traces connected to -IN, and that connections to -IN be kept as short as possible to minimize the capacitance from this node to ground.

Driving Capacitive Loads

Capacitive loads will degrade the amplifier's phase margin resulting in frequency response peaking and possible oscillations. In most cases the oscillation can be avoided by placing an isolation resistor (R) in series with the output as shown in Figure 34.

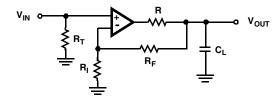


FIGURE 34. PLACEMENT OF THE OUTPUT ISOLATION RESISTOR, R

The selection criteria for the isolation resistor is highly dependent on the load, but 27Ω has been determined to be a good starting value.

Power Dissipation Considerations

Due to the high supply current inherent in dual amplifiers, care must be taken to insure that the maximum junction temperature (T_J , see Absolute Maximum Ratings) is not exceeded. Figure 35 shows the maximum ambient temperature versus supply voltage for the available package styles. It is recommended that thermal calculations, which take into account output power, be performed by the designer.

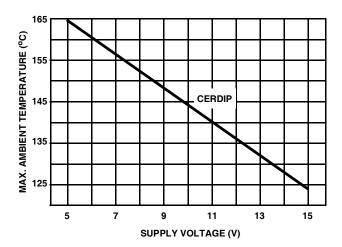


FIGURE 35. MAXIMUM OPERATING AMBIENT TEMPERATURE VS SUPPLY VOLTAGE

Specifications HA5023

DESIGN INFORMATION (Continued)

The information contained in this section has been developed through characterization by Intersil Corporation and is for use as application and design information only. No guarantee is implied.

 $\textbf{Electrical Specifications} \qquad \text{V+} = +5 \text{V}, \ \text{V-} = -5 \text{V}, \ \text{R}_F = 1 \text{k}\Omega, \ \text{A}_V = +1, \ \text{R}_L = 400\Omega, \ \text{C}_L \leq 10 \text{pF}, \ \text{Unless Otherwise Specified}$

	(NOTE 16)		HA5023I				
PARAMETER	TEST LEVEL	TEMPERATURE	MIN	TYP	MAX	UNITS	
INPUT CHARACTERISTICS							
Input Offset Voltage (V _{IO})	А	+25°C	-	0.8	3	mV	
	А	Full	-	-	5	mV	
Delta V _{IO} Between Channels	А	Full	-	1.2	3.5	mV	
Average Input Offset Voltage Drift	В	Full	-	5	-	μV/°C	
V _{IO} Common Mode Rejection Ratio (Note 3)	А	+25°C	53	-	-	dB	
	А	Full	50	-	-	dB	
V _{IO} Power Supply Rejection Ratio (Note 4)	А	+25°C	60	-	-	dB	
	Α	Full	55	-	-	dB	
Input Common Mode Range (Note 3)	А	Full	±2.5	-	-	V	
Non-Inverting Input (+IN) Current	А	+25°C	-	3	8	μΑ	
	Α	Full	-	-	20	μΑ	
+IN Common Mode Rejection (Note 3) $(+I_{BCMR} = \frac{1}{+R_{IN}})$	А	+25°C	-	-	0.15	μ A /V	
$(+ _{BCMR} = \frac{1}{+R_{IN}})$	Α	Full	-	-	0.5	μ A /V	
+IN Power Supply Rejection (Note 4)	А	+25°C	-	-	0.1	μ A /V	
	А	Full	-	-	0.3	μ A /V	
Inverting Input (-IN) Current	А	+25°C, +85°C	-	4	12	μΑ	
	А	-40°C	-	10	30	μΑ	
Delta - IN BIAS Current Between Channels	А	+25°C, +85°C	-	6	15	μΑ	
	А	-40°C	-	10	30	μΑ	
-IN Common Mode Rejection (Note 3)	А	+25°C	-	-	0.4	μ A /V	
	А	Full	-	-	1.0	μ A /V	
-IN Power Supply Rejection (Note 4)	А	+25°C	-	-	0.2	μ A /V	
	Α	Full	-	-	0.5	μ A /V	
Input Noise Voltage (f = 1kHz)	В	+25°C	-	4.5	-	nV/√Hz	
+Input Noise Current (f = 1kHz)	В	+25°C	-	2.5	-	pA/√Hz	
-Input Noise Current (f = 1kHz)	В	+25°C	-	25.0	-	pA/√Hz	
TRANSFER CHARACTERISTICS	•						
Transimpedence (Note 14)	А	+25°C	1.0	-	-	МΩ	
	А	Full	0.85	-	-	МΩ	
Open Loop DC Voltage Gain, $R_L = 400\Omega$, $V_{OUT} = \pm 2.5V$	Α	+25°C	70	-	-	dB	
	А	Full	65	-	-	dB	
Open Loop DC Voltage Gain, $R_L = 100\Omega$, $V_{OUT} = \pm 2.5V$	А	+25°C	50	-	-	dB	
	Α	Full	45	-	-	dB	

Specifications HA5023

DESIGN INFORMATION (Continued)

The information contained in this section has been developed through characterization by Intersil Corporation and is for use as application and design information only. No guarantee is implied.

 $\textbf{Electrical Specifications} \qquad \text{V+ = +5V, V- = -5V, R}_{\text{F}} = 1 \text{k}\Omega, \text{ A}_{\text{V}} = +1, \text{ R}_{\text{L}} = 400\Omega, \text{ C}_{\text{L}} \leq 10 \text{pF}, \text{ Unless Otherwise Specified (Continents)} = 1 \text{ Continents} = 1 \text{ Continents}$

		(NOTE 16)		HA5023I			
PARAMETER		TEST LEVEL	TEMPERATURE	MIN	TYP	MAX	UNITS
Output Voltage Swing (Note 13)		Α	+25°C	±2.5	±3.0	-	V
		Α	Full	±2.5	±3.0	-	V
Output Current (Note 13)		В	Full	±16.6	±20.0	-	mA
Output Current (Short Circuit, Note 10)		Α	Full	±40	±60	-	mA
POWER SUPPLY CHARACTERISTICS		<u>I</u>		I			I.
Supply Voltage Range		Α	+25°C	5	-	15	V
Quiescent Supply Current		Α	Full	-	7.5	10	mA/Op Amp
AC CHARACTERISTICS (A _V = +1)		•			•		
Slew Rate (Note 5)		В	+25°C	275	350	-	V/μs
Full Power Bandwidth (Note 6)		В	+25°C	22	28	-	MHz
Rise Time (Note 7)		В	+25°C	-	6	-	ns
Fall Time (Note 7)		В	+25°C	-	6	-	ns
Propagation Delay (Note 7)		В	+25°C	-	6	-	ns
Overshoot		В	+25°C	-	4.5	-	%
-3dB Bandwidth (Note 8)		В	+25°C	-	125	-	MHz
Settling Time to 1%, 2V Output Step		В	+25°C	-	50	-	ns
Settling Time to 0.25%, 2V Output Step		В	+25°C	-	75	-	ns
AC CHARACTERISTICS ($A_V = +2$, $R_F = 681\Omega$)				•	•		•
Slew Rate (Note 5)		В	+25°C	-	475	-	V/μs
Full Power Bandwidth (Note 6)		В	+25°C	-	26	-	MHz
Rise Time (Note 7)		В	+25°C	-	6	-	ns
Fall Time (Note 7)		В	+25°C	-	6	-	ns
Propagation Delay (Note 7)		В	+25°C	-	6	-	ns
Overshoot		В	+25°C	-	12	-	%
-3dB Bandwidth (Note 8)		В	+25°C	-	95	-	MHz
Settling Time to 1%, 2V Output Step		В	+25°C	-	50	-	ns
Settling Time to 0.25%, 2V Output Step		В	+25°C	-	100	-	ns
Gain Flatness	5MHz	В	+25°C	-	0.02	-	dB
·	20MHz	В	+25°C	-	0.07	-	dB
AC CHARACTERISTICS (A _V = +10, R _F = 383Ω)							
Slew Rate (Note 5)		В	+25°C	350	475	-	V/μs
Full Power Bandwidth (Note 6)		В	+25°C	28	38	-	MHz
Rise Time (Note 7)		В	+25°C	-	8	-	ns
Fall Time (Note 7)		В	+25°C	-	9	-	ns
Propagation Delay (Note 7)		В	+25°C	-	9	-	ns

Specifications HA5023

Electrical Specifications V+=+5V, V-=-5V, $R_F=1k\Omega$, $A_V=+1$, $B_L=400\Omega$, $C_L\leq 10pF$, Unless Otherwise Specified (Continuous)

	(NOTE 16)		HA5023I			
PARAMETER	TEST LEVEL	TEMPERATURE	MIN	TYP	MAX	UNITS
Overshoot	В	+25°C	-	1.8	-	%
-3dB Bandwidth (Note 8)	В	+25°C	-	65	-	MHz
Settling Time to 1%, 2V Output Step	В	+25°C	=	75	-	ns
Settling Time to 0.1%, 2V Output Step	В	+25°C	-	130	=	ns
VIDEO CHARACTERISTICS						
Differential Gain (Notes 11, 13)	В	+25°C	-	0.03	-	%
Differential Phase (Notes 11, 13)	В	+25°C	-	0.03	-	Degrees

NOTES:

- 1. Absolute maximum ratings are limiting values, applied individually, beyond which the serviceability of the circuit may be impaired. Functional operation under any of these conditions is not necessarily implied.
- 2. Output is protected for short circuits to ground. Brief short circuits to ground will not degrade reliability, however, continuous (100% duty cycle) output current should not exceed 15mA for maximum reliability.
- 3. $V_{CM} = \pm 2.5V$. At -40°C Product is tested at $V_{CM} = \pm 2.25V$ because Short Test Duration does not allow self heating.
- 4. $\pm 3.5 \text{V} \le \text{V}_{\text{S}} \le \pm 6.5 \text{V}$
- 5. V_{OUT} switches from -2V to +2V, or from +2V to -2V. Specification is from the 25% to 75% points.
- 6. FPBW = $\frac{\text{Slew Rate}}{2\pi V_{\text{PEAK}}}$; $V_{\text{PEAK}} = 2V$
- 7. R_L = 100Ω, V_{OUT} = 1V. Measured from 10% to 90% points for rise/fall times; from 50% points of input and output for propagation delay.
- 8. $R_L = 400\Omega$, $V_{OUT} = 100$ mV.
- 9. A. Production Tested; B. Guaranteed Limit or Typical based on characterization; C. Design Typical for information only.
- 10. $V_{IN} = \pm 2.5V$, $V_{OUT} = 0V$.
- 11. Measured with a VM700A video tester using an NTC-7 composite VITS.
- 12. Maximum power dissipation, including output load, must be designed to maintain junction temperature below +175°C for die, and below +150°C for plastic packages. See Applications Information section for safe operating area information.
- 13. $R_1 = 150\Omega$.
- 14. $V_{OUT} = \pm 2.5V$. At -40°C Product is tested at $V_{OUT} = \pm 2.25V$ because Short Test Duration does not allow self heating.
- 15. ESD protection is for human body model tested per MIL-STD 883, Method 3015.7.
- 16. A. Production Tested; B. Guaranteed limit or Typical based on characterization; C. Design Typical for information only.

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